

Silicon PNP Power Transistors

2SB891F

DESCRIPTION

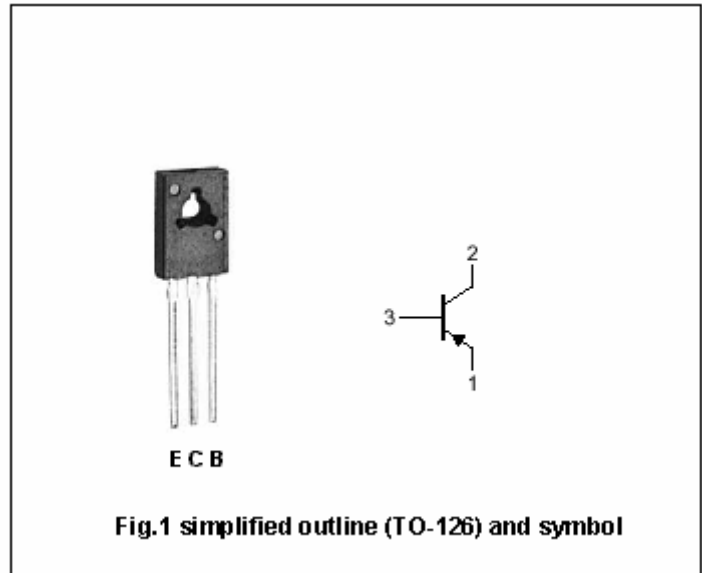
- With TO-126 package
- Complement to type 2SD1189F
- Low collector saturation voltage

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-40	V
V_{CEO}	Collector-emitter voltage	Open base	-32	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-2	A
I_{CM}	Collector current-Peak		-3	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	1.2	W
		$T_C=25^\circ\text{C}$	5	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA ; I _B =0	-32			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-50 μ A ; I _E =0	-40			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-50 μ A ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2.0A ; I _B =-0.2A		-0.5	-0.8	V
I _{CBO}	Collector cut-off current	V _{CB} =-20V ; I _E =0			-1.0	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-4V ; I _C =0			-1.0	μ A
h _{FE}	DC current gain	I _C =-0.5A ; V _{CE} =-3V	82		390	
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-5V ; f=30MHz		100		MHz
C _{OB}	Collector output capacitance	I _E =0 ; f=1MHz ; V _{CB} =-10V		50		pF

◆ h_{FE-2} Classifications

P	Q	R
82-180	120-270	180-390

PACKAGE OUTLINE

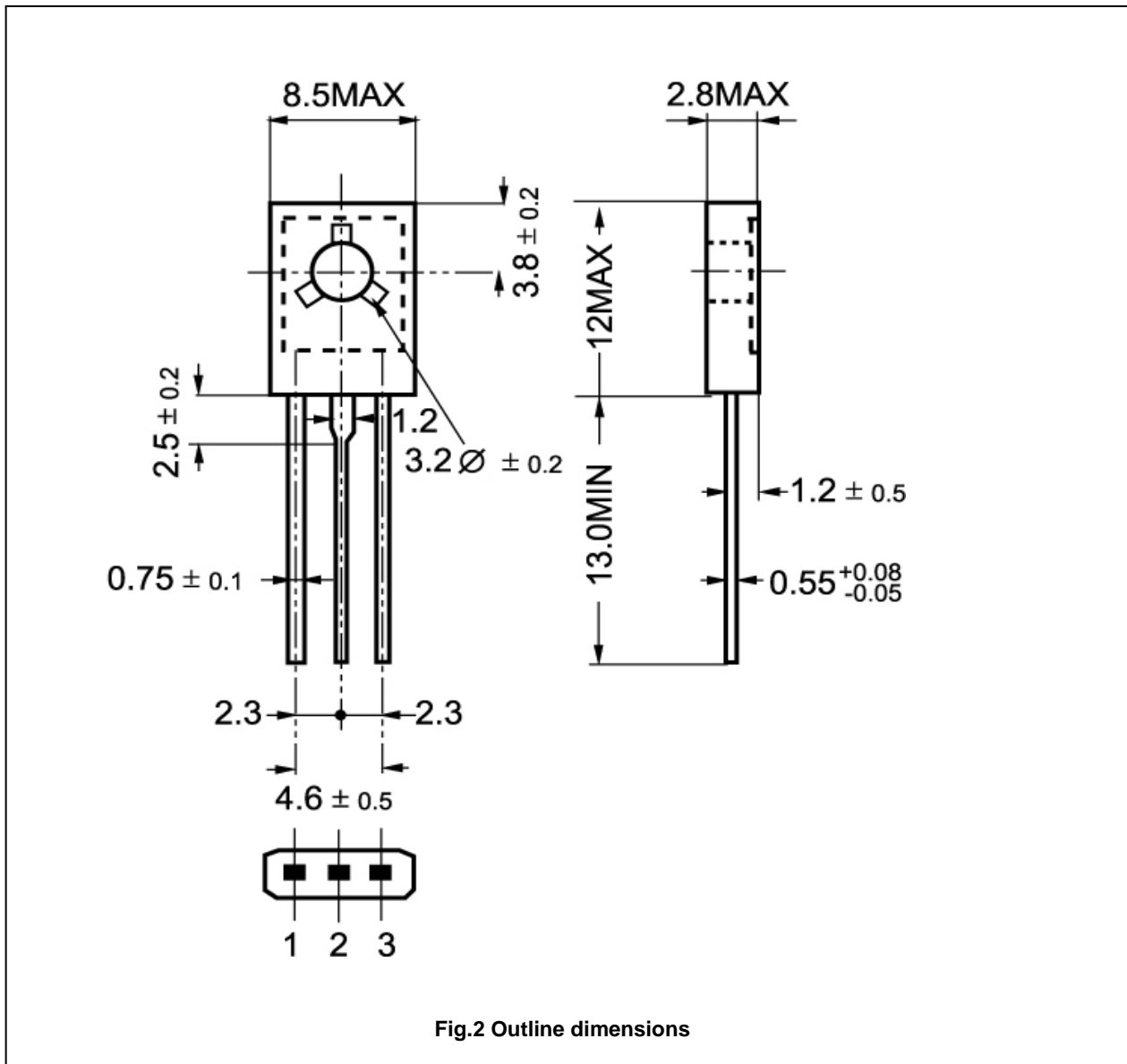


Fig.2 Outline dimensions